Vishay Semiconductors

8-Line ESD-Protection Diode Array in LLP1713-9L

RoHS COMPLIANT

GREEN

(5-2008)

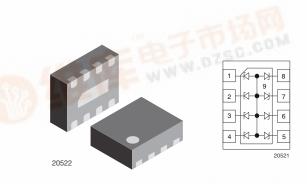
Features

- Ultra compact LLP1713-9L package
- Low package profile < 0.6 mm
- 8-line ESD-protection

查询"VESD05A8A-HNH"供应商

- Low leakage current I_R < 1 μA
- Low load capacitance C_D = 30 pF
- ESD-immunity acc. IEC 61000-4-2 ± 25 kV contact discharge ± 30 kV air discharge
- Working voltage range V_{RWM} = 5 V
- e4 precious metal (e.g. Ag, Au, NiPd, NiPdAu) (no Sn)
- · Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

20719



Dot = Pin 1 marking Y = Type code (see table below)

XX = Date code

Ordering Information

Marking (example only)

Device name	Ordering code	Taped units per reel (8 mm tape on 7" reel)	Minimum order quantity		
VESD05A8A-HNH	VESD05A8A-HNH-GS08	3000	15 000		

Package Data

Device name	Package name	Marking code	Weight	Molding compound flammability rating	Moisture sensitivity level	Soldering conditions
VESD05A8A-HNH	LLP1713-9L	В	3.7 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals

** Please see document "Vishay Material Category Policy" www.vishay.com/doc?99902

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Absolute Maximum Ratings

Rating	Test conditions	Symbol	Value	Unit	
Deck pulse ourrent	BiAs-mode: each input (pin 1 - pin 8) to ground (pin acc. IEC 61000-4-5; t _p = 8/20 μs; single shot	I _{PPM}	5	А	
Peak pulse current	BiSy-mode: each input (pin 1 - pin 8) to any other inp Pin 9 not connected. Acc. IEC 61000-4-5; $t_p = 8/20 \ \mu s$; s	I _{PPM}	2.5	А	
Peak pulse power	BiAs-mode: each input (pin 1 - pin 8) to ground (pin acc. IEC 61000-4-5; t _p = 8/20 μs; single shot	P _{PP}	65	W	
	BiSy-mode: each input (pin 1 - pin 8) to any other inp Pin 9 not connected. Acc. IEC 61000-4-5; $t_p = 8/20 \ \mu s$; s	P _{PP}	33	W	
ESD-immunity	Acc. IEC61000-4-2; 10 pulses BiAs-mode: each input (pin 1 - pin 8) to ground (pin 9)	Contact discharge	V _{ESD}	± 25	kV
		Air discharge	V _{ESD}	± 30	kV
	Acc. IEC 61000-4-2 ; 10 pulses BiSy-mode: each input (pin 1 - pin 8) to any other input pin.	Contact discharge	V _{ESD}	± 12	kV
	Pin 9 not connected.	Air discharge	V _{ESD}	± 12	kV
Operating temperature	Junction temperature			- 40 to + 125	°C
Storage temperature	ature			- 55 to + 150	°C

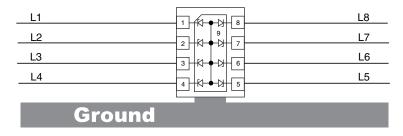
BiAs-Mode (8-line Bidirectional Asymmetrical protection mode)

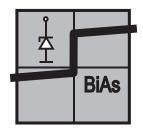
With the **VESD05A8A-HNH** up to 8 signal- or data-lines (L1 - L8) can be protected against voltage transients. With pin 9 connected to ground and pin 1 up to pin 8 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified **M**aximum **R**everse **W**orking **V**oltage (**V**_{**RWM**}) the protection diode between data line and ground offer a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage (V_C) is defined by the **BR**eakthrough Voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low Forward Voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the **VESD05A8A-HNH** clamping behaviour is **<u>Bi</u>directional and <u>As</u>ymmetrical (BiAs**).





20524



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Electrical Characteristics

Ratings at 25 °C, ambient temperature unless otherwise specified

VESD05A8A-HNH

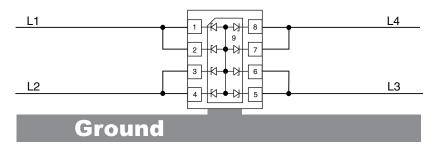
BiAs mode: each input (pin 1 - pin 8) to ground (pin 9)

Parameter	Test conditions/remarks	Symbol	Min.	Тур.	Max.	Unit
Protection paths	Number of line which can be protected	N lines			8	lines
Reverse current	at I _R = 1 μA	V _{RWM}	5			V
Max. reverse current	at $V_{R} = V_{RWM} = 5 V$	I _R		< 0.1	1	μA
Min. reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6		8	V
Max. clamping voltage	at I _{PP} = 5 A acc. IEC 61000-4-5	V _C			13	V
Max. forward clamping voltage	at I _F = 5 A acc. IEC 61000-4-5	V _F			4.5	V
Line capacitance	at $V_{R} = 0 V$; f = 1 MHz	CD		30	35	pF
	at V _R = 2.5 V; f = 1 MHz	CD		18	23	pF

If a higher surge current or **P**eak **P**ulse **current** (**I**_{**PP**}) is needed, some protection diodes in the **VESD05A8A-HNH** can also be used in parallel in order to "multiply" the performance.

If two diodes are switched in parallel you get

- double surge power = double peak pulse current (2 x I_{PPM})
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line Capacitance (2 x C_D)
- double Reverse leakage current (2 x I_R)



20525

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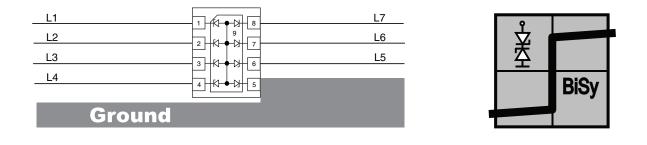


BiSy-mode (7-line Bidirectional Symmetrical protection mode)

If a bipolar symmetrical protection device is needed the **VESD05A8A-HNH** can also be used as a seven-line protection device. Therefore seven pins (example: pin 1, 2, 3, 4, 6, 7 and 8) has to be connected to the signal-or data-line (L1 - L7) and pin 5 to ground. Pin 9 must not be connected!

Positive and negative voltage transients will be clamped in the same way. The clamping current from one data line through the **VESD05A8A-HNH** to the ground passes one diode in forward direction and the other one in reverse direction. The **C**lamping Voltage (V_C) is defined by the **BR**eakthrough Voltage (V_{BR}) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the **VESD05A8A-HNH** voltage clamping behaviour is also **<u>Bi</u>**directional and **<u>Sy</u>**mmetrical (**BiSy**).



20526_1

Electrical Characteristics

Ratings at 25 °C, ambient temperature unless otherwise specified

VESD05A8A-HNH

BiSy mode: each input (pin 1 - pin 8) to any other input pin connected to ground; pin 9 not connected

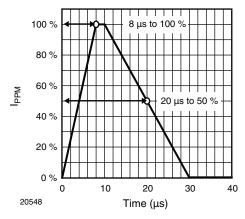
Parameter	Test conditions/remarks	Symbol	Min.	Тур.	Max.	Unit
Protection paths	Number of line which can be protected	N _{lines}			7	lines
Reverse current	at I _R = 1 μA	V _{RWM}	5.5			V
Max. reverse current	at $V_{R} = V_{RWM} = 5.5 V$	I _R		< 0.1	1	μA
Min. reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6.5		8.7	V
Max. clamping voltage	at I _{PP} = 2.5 A acc. IEC 61000-4-5	V _C			13	V
Line capacitance	at V _R = 0 V; f = 1 MHz	CD		15	18	pF
	at V _R = 2.5 V; f = 1 MHz	CD		13	15	pF

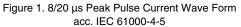


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Typical Characteristics

T_{amb} = 25 °C, unless otherwise specified





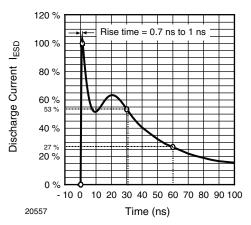


Figure 2. ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω/150 pF)

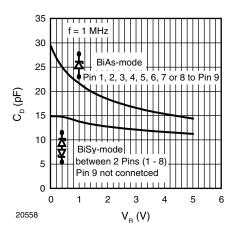


Figure 3. Typical Capacitance C_D vs. Reverse Voltage V_R

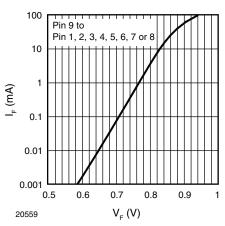
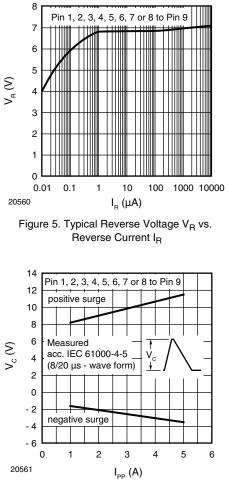
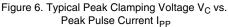


Figure 4. Typical Forward Current I_F vs. Forward Voltage V_F





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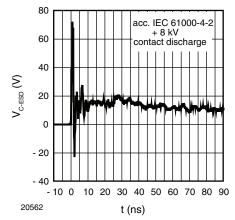


Figure 7. Typical Clamping Performance at + 8 kV Contact Discharge (Acc. IEC 61000-4-2)

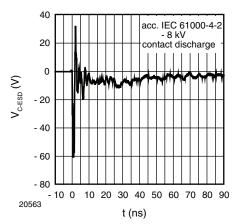


Figure 8. Typical Clamping Performance at - 8 kV Contact Discharge (acc. IEC 61000-4-2)

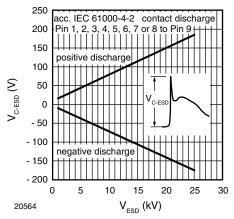


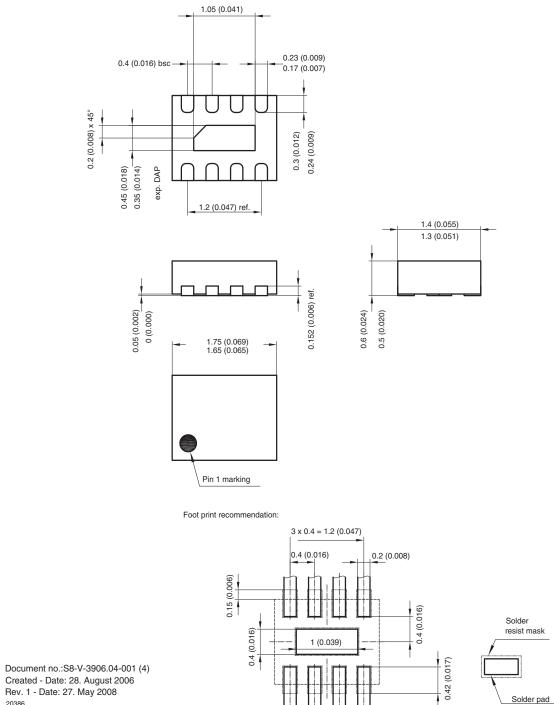
Figure 9. Typical Peak Clamping Voltage at ESD Contact Discharge (acc. IEC 61000-4-2)



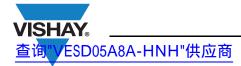


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Package Dimensions in millimeters (inches): LLP1713-9L



20386



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